

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions and listings of claims in the application:

LISTING OF CLAIMS

1. (Currently Amended) A method of forming a metal line layer in a semiconductor device, comprising the steps of:

depositing a metal line layer having ~~a plurality of~~ first, second and third conductive layers on a semiconductor structure;

depositing an insulating film on the third conductive layer;

depositing and patterning a photosensitive material on the ~~metal line layer~~ insulating film;

etching ~~at least one~~ the insulating film, the third and second conductive ~~layer~~ layers ~~of the plurality of conductive layers~~ using the photosensitive material as a mask;

removing the photosensitive material;

forming a side wall oxide film on a the ~~side wall~~ walls of the ~~at least one~~ second conductive layer ~~of the etched conductive layers~~;

and

etching the ~~non-etched~~ first conductive layer ~~of the conductive layers constituting the metal line layer~~ using the insulating film as a hard mask.

2. (Currently Amended) A method of forming a metal line layer in a semiconductor device according to claim 1, wherein ~~at least one of the~~ second conductive layers is made of aluminum (Al).

3. (Currently Amended) A method of forming a metal line layer in a semiconductor device according to claim ~~2~~ 1, wherein the metal line layer is formed by laminating a first Ti/TiN layer, an Al layer and a second Ti/TiN layer in this order, and the side wall oxide film is an Al<sub>2</sub>O<sub>3</sub> film, ~~and the non-etched conductive layers are the first Ti/TiN layer which is a lowermost layer.~~

4. (Currently Amended) A method of forming a metal line layer in a semiconductor device according to claim ~~3~~ 1, wherein the ~~Ti/TiN layers~~ insulating film, the third and second conductive layers are dry-etched using activated plasma comprising Cl<sub>2</sub>/ BCl<sub>3</sub> /N<sub>2</sub> gas.

5. (Canceled)

6. (Currently Amended) A method of forming a metal line layer in a semiconductor device according to claim ~~5~~ 1, wherein the insulating film is a nitride film, ~~and the metal line layer is formed~~

~~by laminating a first Ti/TiN layer, an Al layer and a second Ti/TiN layer in this order.~~

7. (Currently Amended) A method of forming a metal line layer in a semiconductor device according to claim 5 1, wherein the insulating film is etched by means of a dry etching process using activated plasma comprising a combination of  $\text{CHF}_3$  /  $\text{CF}_4$  /Ar or /  $\text{C}_x\text{F}_y$  (where x, y are natural numbers) /  $\text{O}_2$  /Ar gas.

8. (Canceled)